

ABSTRACT

It is an object of the present invention to make it possible to decrease the on-state resistance of a selection transistor of a memory cell without increasing the whole area of a memory cell array and accelerate and stabilize the reading operation of data stored in the memory cell. Therefore, a plurality of variable resistive elements capable of storing information in accordance with a change of electrical resistances is included, one ends of the variable resistive elements are connected each other, and an electrode of a selection element constituted by a MOSFET or diode element for selecting the variable resistive elements in common is connected with one end of each of the variable resistive elements to constitute a memory cell .

Reference drawing: Fig. 1